

1 (currently amended). A method for hermetically sealing of dielectrically
 2 insulating isolation trenches by filling with a fill material in a deposition method,
 3 wherein each of the trenches has a first width (b1) and is ~~are~~ slightly
 4 broadened (b2) at a specific position (2) and trench portion longitudinally
 5 adjacent to the first width, wherein a low pressure deposition technique is
 6 used such that a void channels (5) forming is formed in the an area of the
 7 each trenches having ~~normal~~ the first width (b1) by closing the an upper trench
 8 portions with the a fill material (9) ~~are~~ and hermetically sealed each trench in
 9 the a longitudinal direction of the trench by means of by low pressure material
 10 deposition from the broadened trench portion and along the length direction of
 11 the each trench.

2(cancelled).

1 3(previously presented). The method of claim 1, wherein the broadened
 2 trench portions are provided in regular intervals.

4(cancelled).

1 5(currently amended). A method for hermetically sealing
 2 dielectrically insulating isolation trenches by filling with a low pressure
 3 deposition technique,

4 (i) wherein the each isolation trenches ~~are~~ has two portions of a first
 5 width, both being slightly broadened towards at least ~~at least at one specific~~
 6 ~~position~~ broader trench portion that is longitudinally between the two
 7 portions of the first width;

8 (ii) ~~a~~ said low pressure deposition technique is used to hermetically seal
 9 a void in a longitudinal direction of the isolation trench by ~~means of a~~ said low
 10 pressure material deposition starting from the at least one broadened trench

11 portion ~~(2, 3)~~ **and** along ~~the~~ **a** length direction of the trench, wherein said void ~~is~~
 12 **was** formed in ~~the area of the~~ **each** isolation trenches ~~(1)~~ **portion** having the
 13 ~~normal~~ **first** width **and** due to the closure of **the** upper trench portions **of first**
 14 **width** with **said** fill material.

6(cancelled).

1 7(previously presented). The method of claim 5, wherein a plurality of
 2 broadened trench portions are provided in regular intervals for forming sealing
 3 positions along a channel.

1 8(previously presented). The method of claim 5, wherein the slightly
 2 broadened isolation trenches are broadened at the at least at one position
 3 according to a width that is not greater than the width of the trench at the non-
 4 broadened position.

1 9(currently amended). The method of claim 5, wherein ~~the~~ **each**
 2 broadened ~~ing trench portion~~ **trench portion** ~~(2, 3)~~ is provided by **two** conical sections ~~(3)~~,
 3 **starting from the first width portions of each trench.**

1 10(previously presented). The method of claim 5, wherein the low
 2 pressure technique is performed substantially at vacuum conditions.

1 11(previously presented). The method of claim 5, wherein the
 2 broadening is provided at least at a short piece compared to the total length of
 3 the channel.

1 12(currently amended). The method of claim 5, wherein the selection of
 2 parameters of the deposition process and of a trench configuration is performed
 3 such that possibly remaining lateral voids are completely sealed before the

4 slightly broadened trench ~~section having the slight broadening (b2)~~ portion is
 5 closed ~~in the~~ an upwards direction, ~~so that a~~ inhibiting further filling ~~cannot~~
 6 ~~take place~~ of the trench.

1 13(currently amended). A device comprising a wafer having formed
 2 therein isolation trenches, said wafer including hermetically sealed dielectrically
 3 insulating isolation trenches formed by filling with a low pressure deposition
 4 method,

5 (i) wherein ~~the~~ each isolation trenches ~~(1, 2) are~~ is slightly broadened
 6 at least at one specific ~~position~~ portion between at least two conical portions
 7 towards two portions of a smaller width than said broadened width;

8 (ii) wherein void channels are hermetically sealed in the longitudinal
 9 direction of ~~the~~ each trench by ~~a~~ said low pressure material deposition from the
 10 broadened trench portion in the longitudinal direction of the trench filled by
 11 means of ~~a~~ the low pressure deposition technique, said void channels ~~being~~
 12 having formed during the filling in ~~the area of~~ the trenches having the ~~normal~~
 13 smaller width by closing the upper trench portions with fill material.

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